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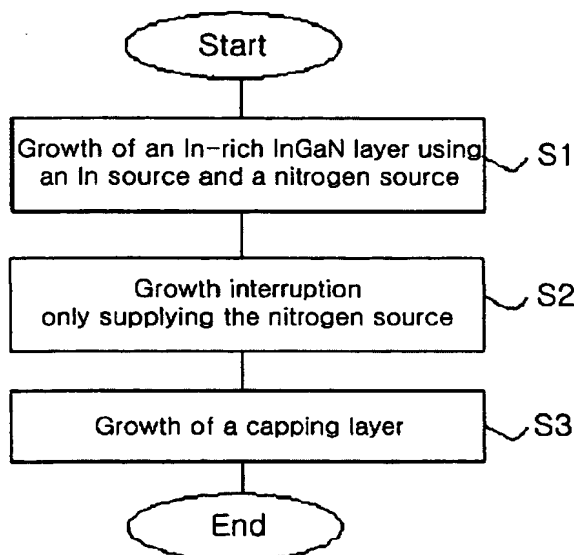
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(54) Title: GROWTH METHOD OF NITRIDE SEMICONDUCTOR LAYER AND LIGHT EMITTING DEVICE USING THE GROWTH METHOD



(57) Abstract: The present invention relates to a growth method of nitride semiconductor layer comprising a first step for growing a first nitride semiconductor layer on an $\text{Al}_x\text{Ga}_{1-x}\text{In}_{1-y}\text{N}$ ($0 < x < 1$, $0 < y < 1$, $0 < x+y < 1$) layer, a second step for reducing the thickness of the first nitride semiconductor layer by growth interruption and, a third step for growing a second nitride semiconductor layer having a band gap energy higher than that of the first nitride semiconductor layer on the first nitride semiconductor layer with the reduced thickness and a light emitting device using the growth method.

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